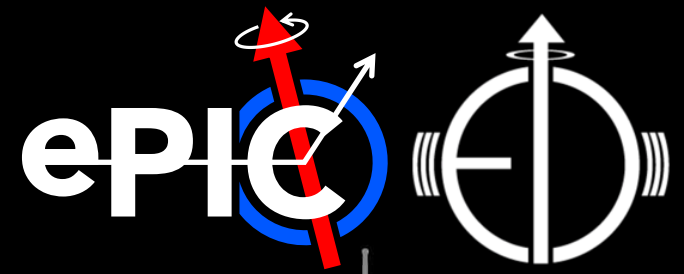




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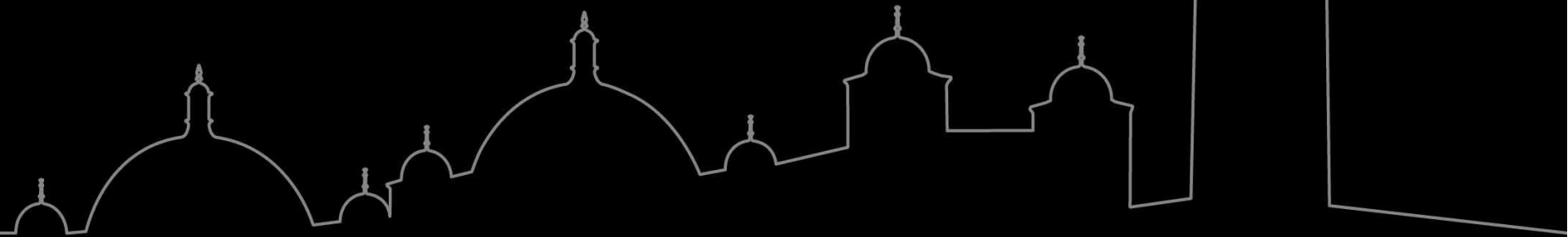


ePIC SVT OB FPC Implications

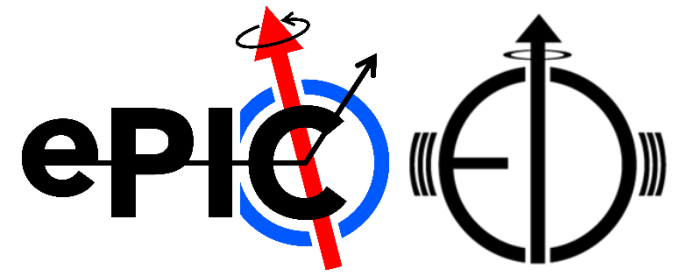
James Glover

EIC-UK WP1 (MAPS)

Wed, 6th November 2024

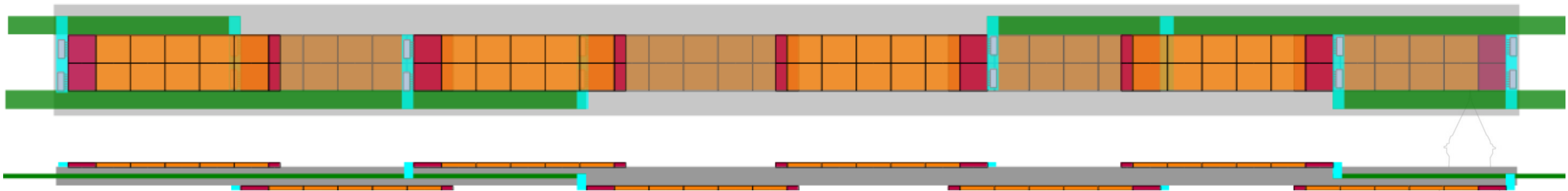


Previous OB EIC-LAS groupings

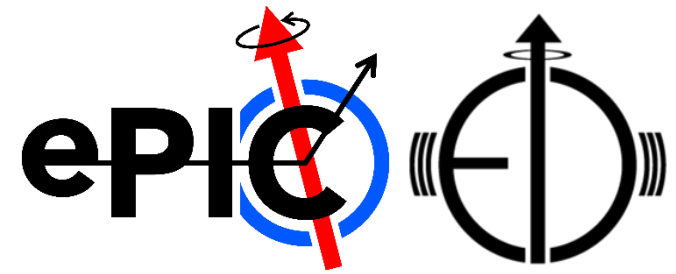


- Minimising the material and (main)FPC length was a priority.
- Lead to designs and groups that linked EIC-LAS on both stave surfaces.

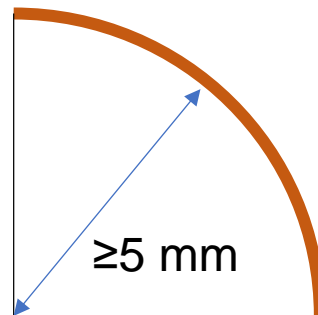
Layer 4 (EIC-LAS w. 5*RSU)



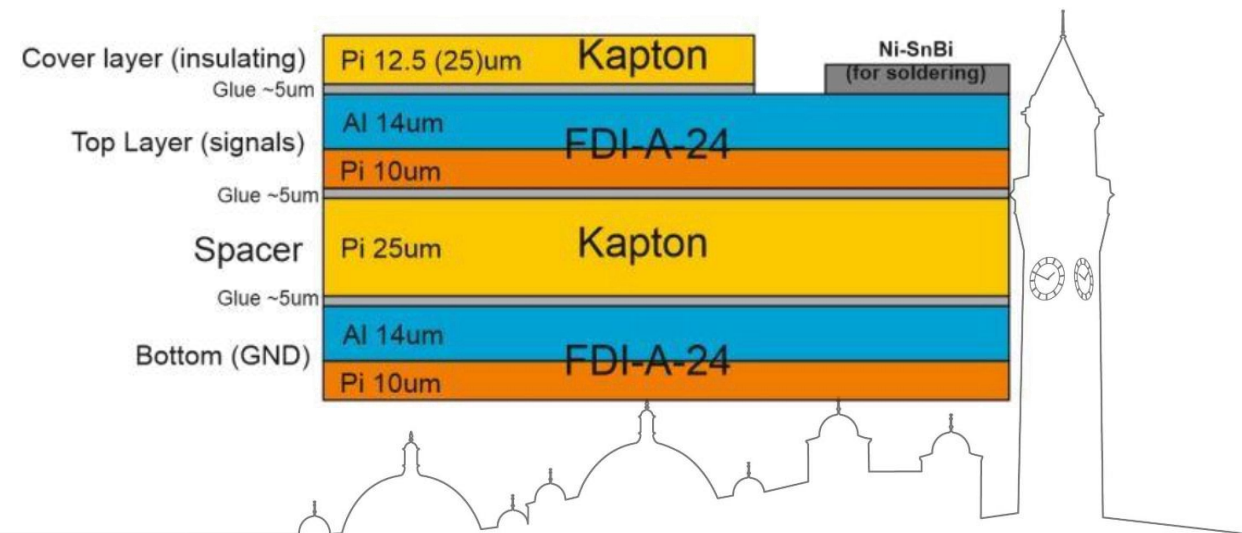
FPC bend radius



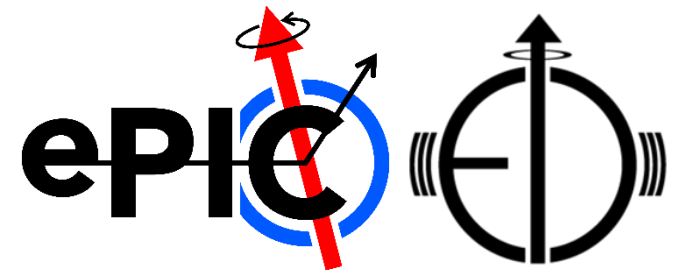
- The FPCs from LTU have a stack up of Kapton (25 μm), glue (5 μm), and aluminium foil (14 μm + 10 μm support).
- \approx (110 μm) total thickness.
- The composition of this stack up limits the flexibility of the circuit.
- A minimum bend radius of 5mm has been stated to prevent the aluminium foil from fracturing within the stack up.



Base cross-section of M-FPC and B-FPCs



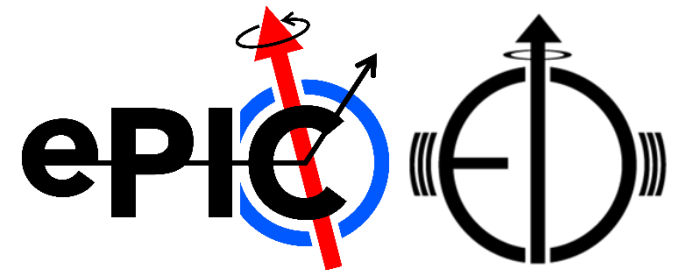
Stave thickness



- Current (curved) staves have \approx (4 mm) between silicon of edge of stave – thickest (central) point of stave is \approx (8 mm).
- Planned flat stave thickness is \approx (6 mm), to keep similar volume for airflow.
- FPC bend radius dictates a stave thickness of >10 mm (assuming 180° of rotation).
- The **FPC bend radius makes interconnection between stave faces impractical!**

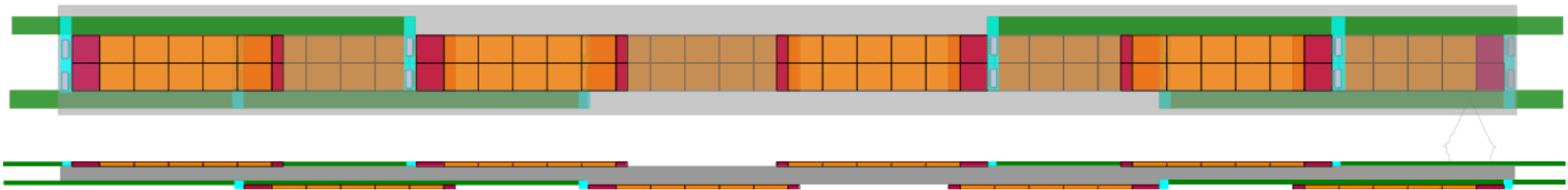


New OB EIC-LAS groupings

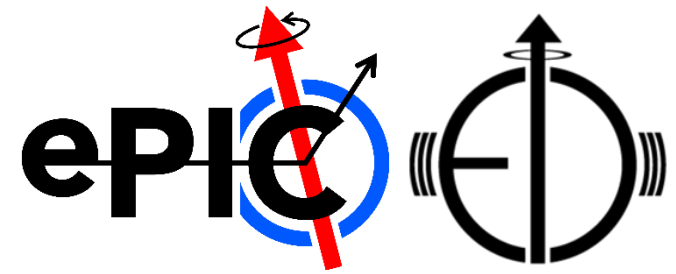


- To keep the stave thickness (and associated material) minimal, we need all EIC-LAS groups by 1 (main)FPC to be on the same stave side.
- Not too problematic for L4.

Layer 4 (EIC-LAS w. 5*RSU)

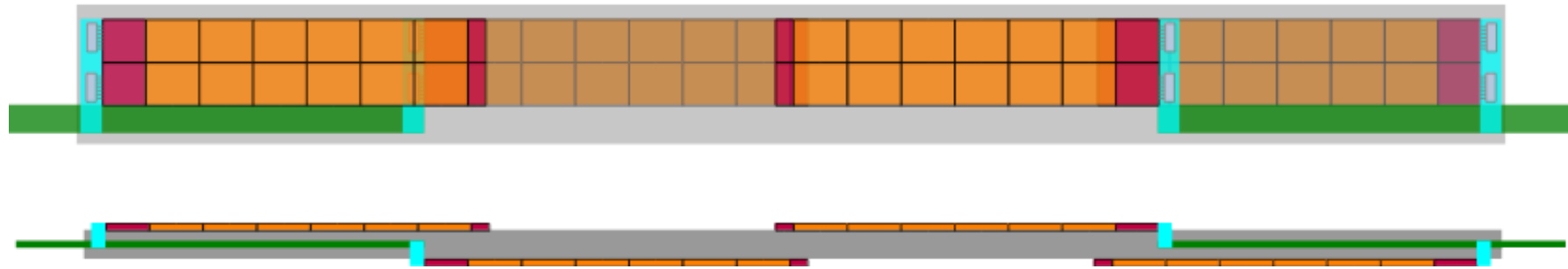


L3 adds complications



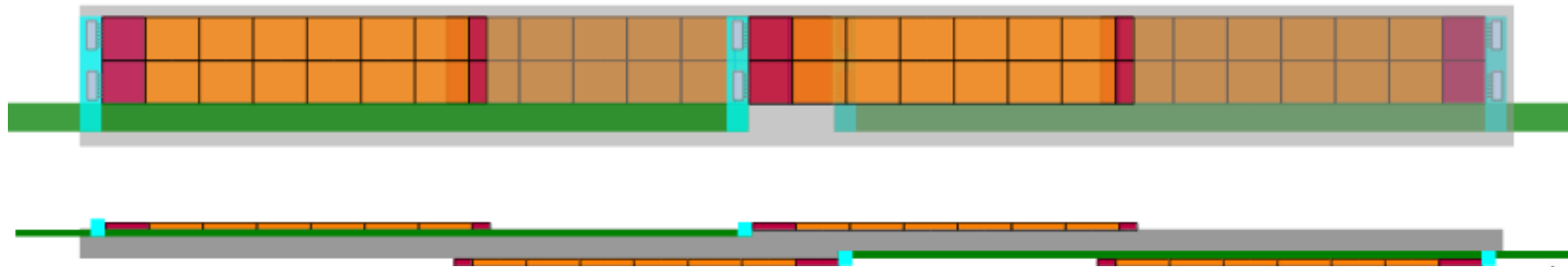
Previously, convenient for low material around IP

Layer 3 (EIC-LAS w. 6*RSU)

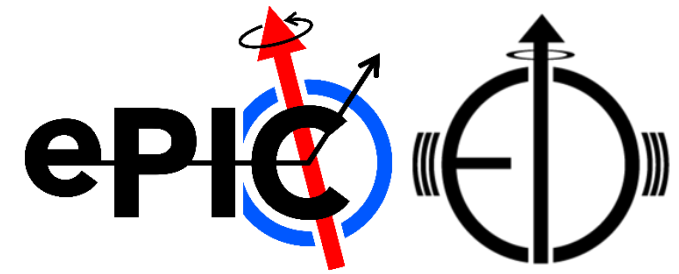


New (potential) groupings, **more material** (around IP and more FPC)!

Layer 3 (EIC-LAS w. 6*RSU)

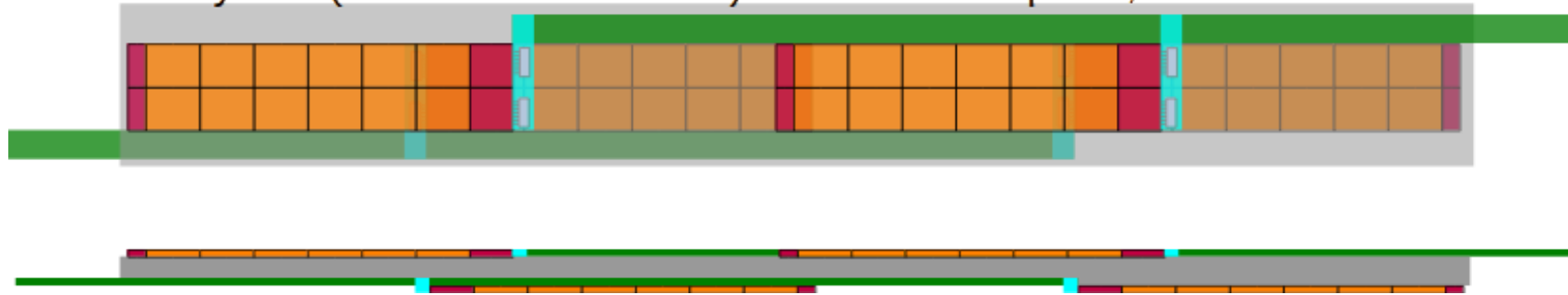


Alternative L3 options



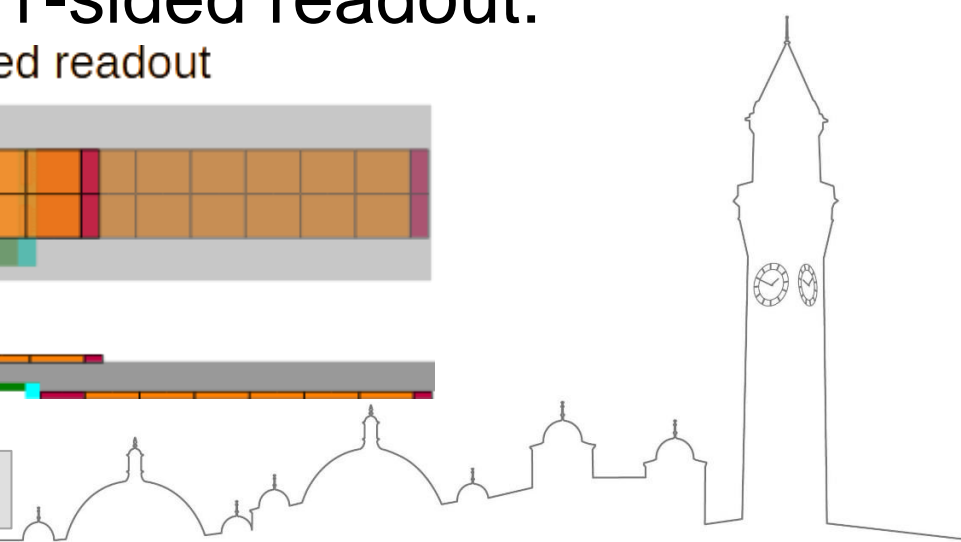
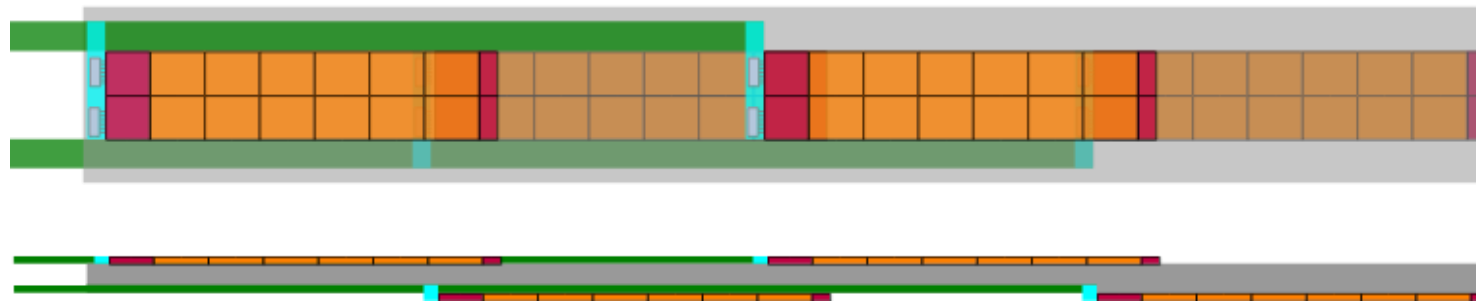
Less silicon around the IP and dead space at stave ends (more FPC):

Layer 3 (EIC-LAS w. 6*RSU) – less dead space, more material

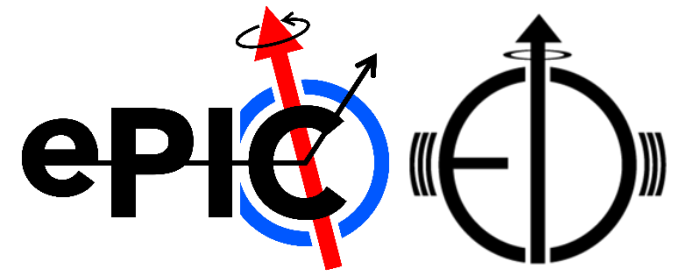


Simplest construction (e.g. 1/2 L4 style), with 1-sided readout:

Layer 3 (EIC-LAS w. 6*RSU) – 1-sided readout



Bridge FPC (module) testing

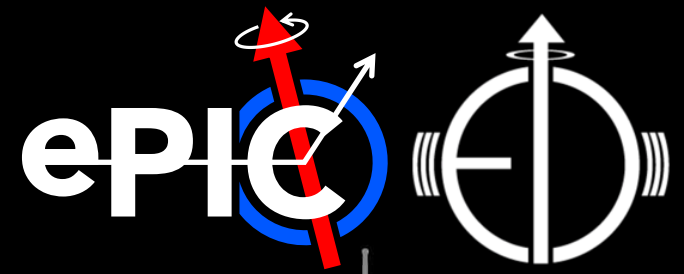


- How do we test modules (2 EIC-LAS) through the (bridge)FPC?
- If we bond the (bridge)FPC to a test board, the bond area will not be reusable, \therefore it cannot be the same bond area as intended for the interconnection with the (main)FPC.
- 14 μm of aluminium is (probably) too fragile to probe.
- We need dedicated test pads on the (bridge)FPC.
 - How many times will we test a stand-alone module?
 - Will we need a sacrificial extension for the (bridge)FPC for testing?
 - Is this then cut off when mounting the module to the stave (to save material)?
 - Need a reliable cutting procedure to not damage the module and/or stave.



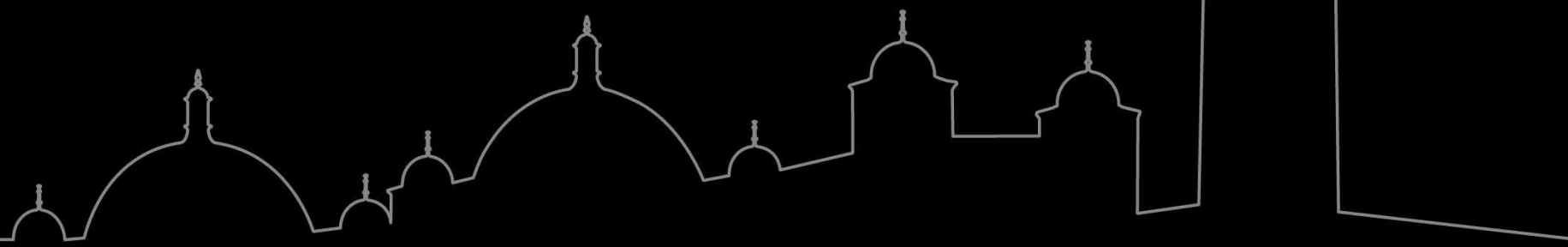


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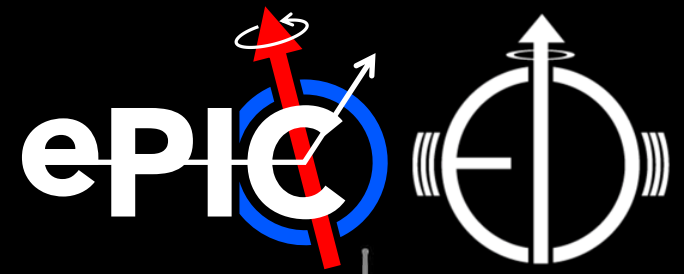
Thank you very much!

Any questions?

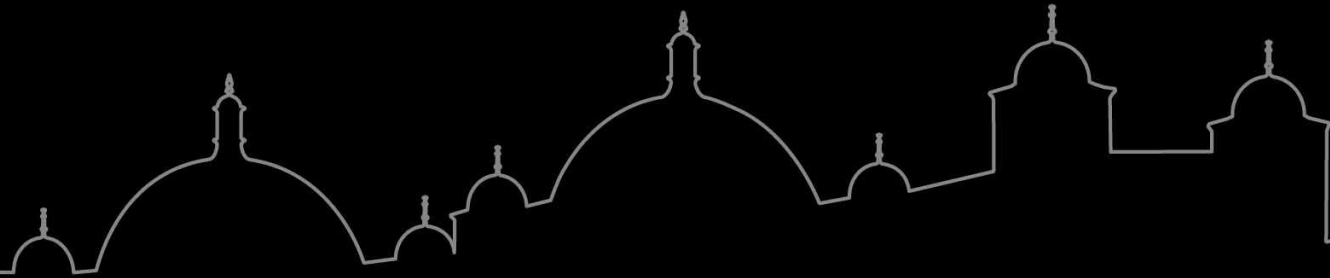




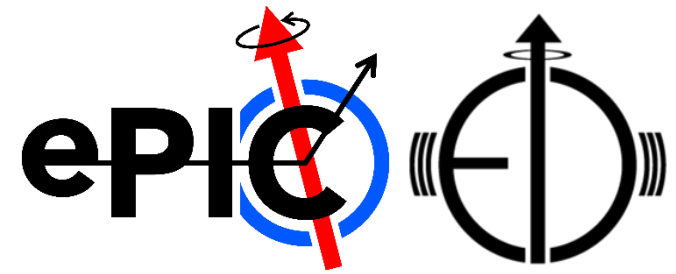
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Additional (support) slides

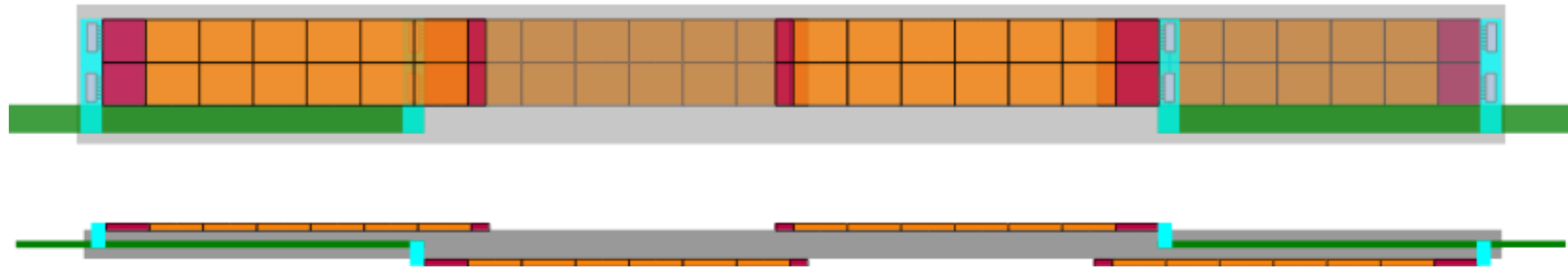


L3 adds complications



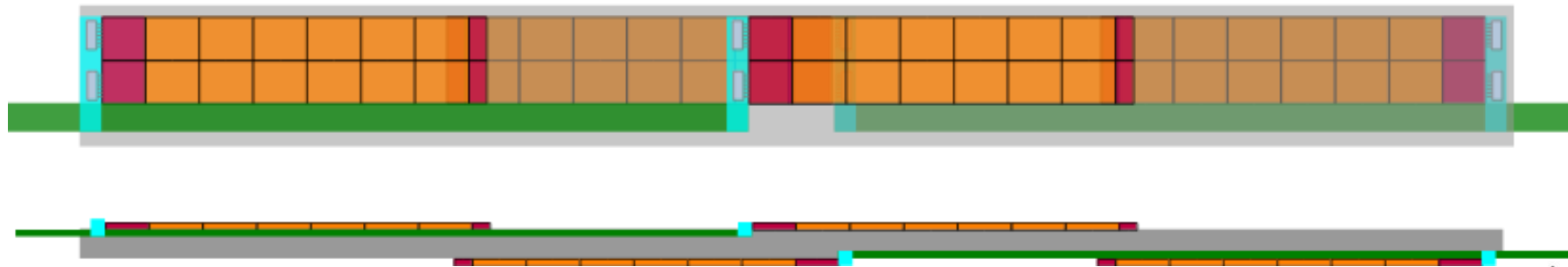
Previously, convenient for low material around IP

Layer 3 (EIC-LAS w. 6*RSU)

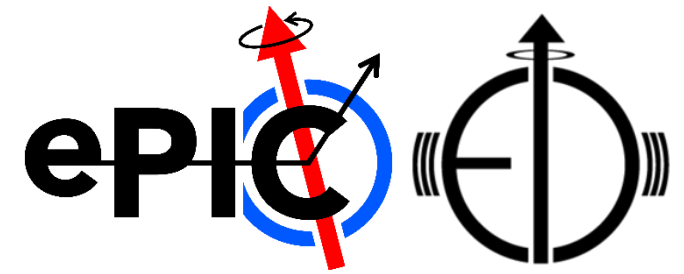


New (potential) groupings, **more material** (around IP and more FPC)!

Layer 3 (EIC-LAS w. 6*RSU)

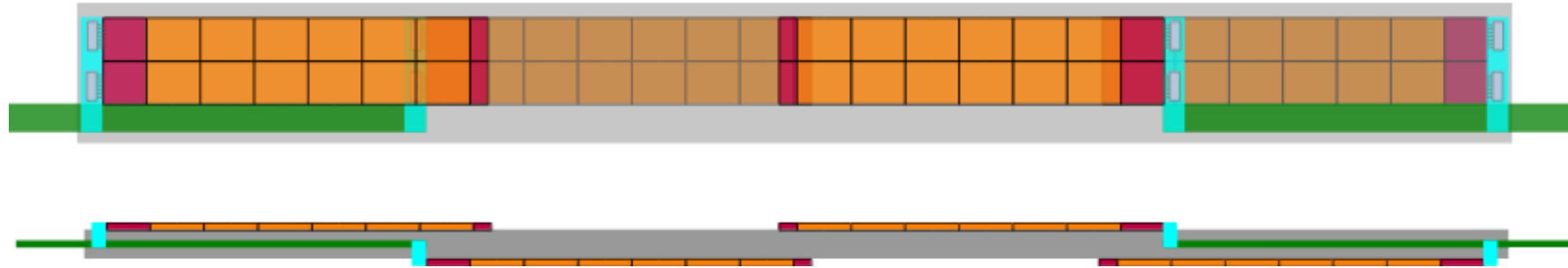


Compare L3 (less dead space)



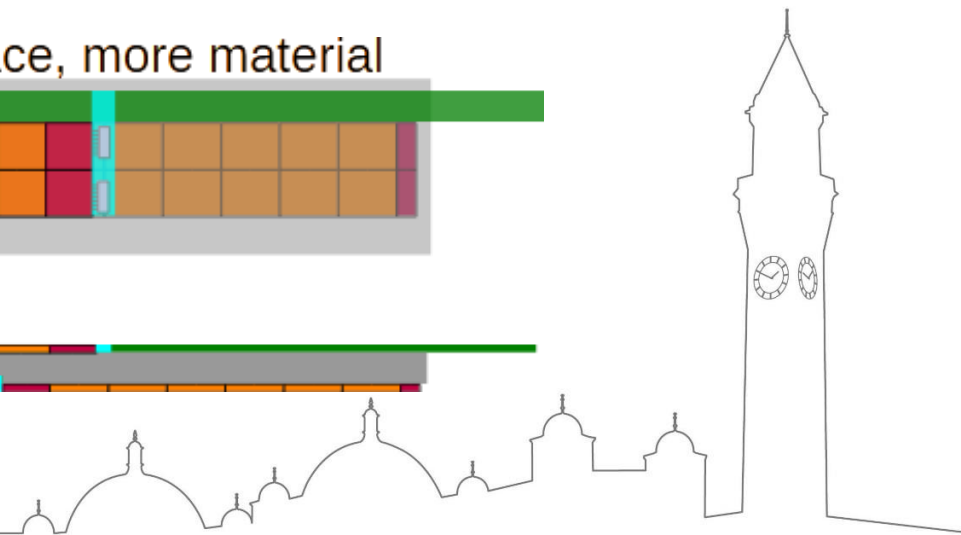
Previous groupings:

Layer 3 (EIC-LAS w. 6*RSU)

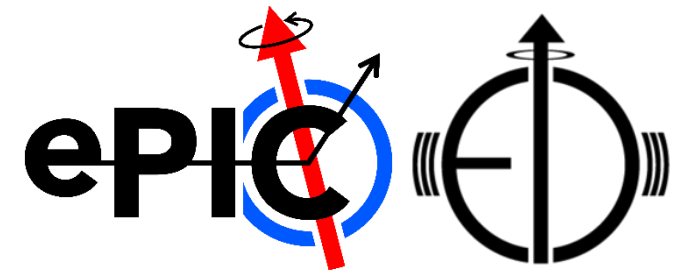


Less dead space (more material):

Layer 3 (EIC-LAS w. 6*RSU) – less dead space, more material

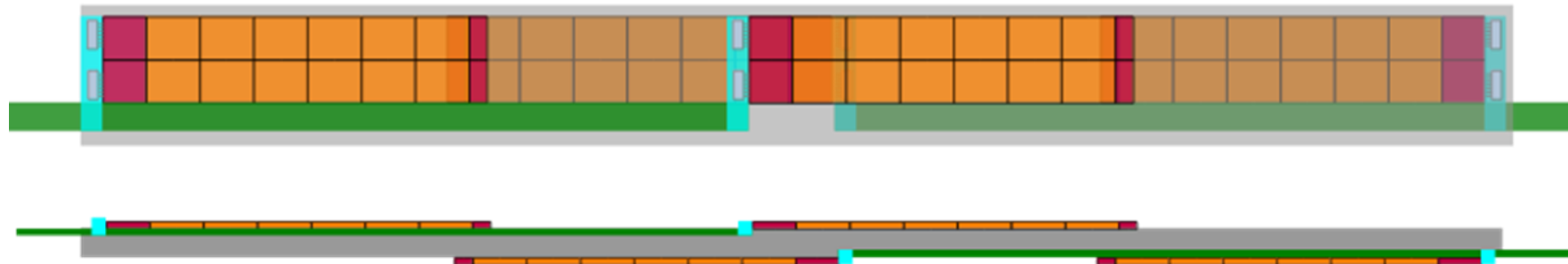


Compare L3 (newer groupings)



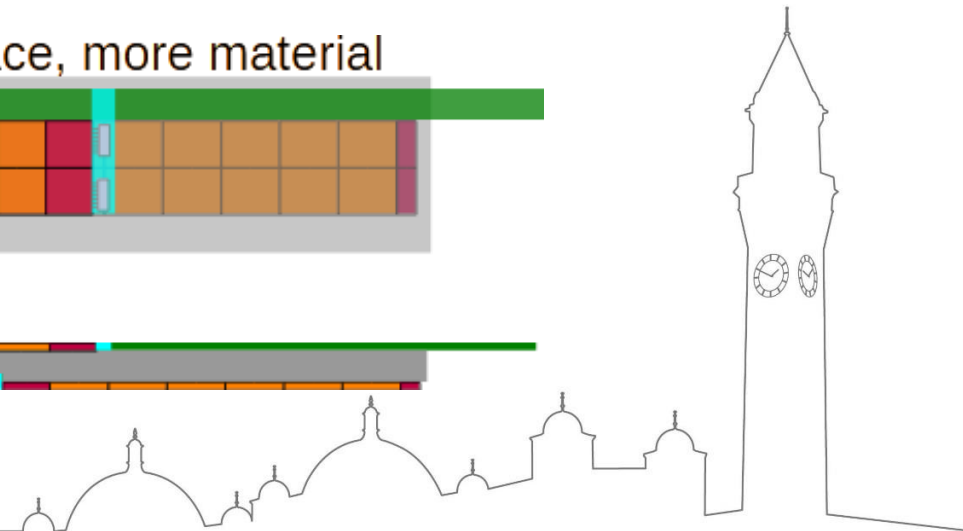
New (potential) groupings, **more material** (around IP and more FPC)!

Layer 3 (EIC-LAS w. 6*RSU)

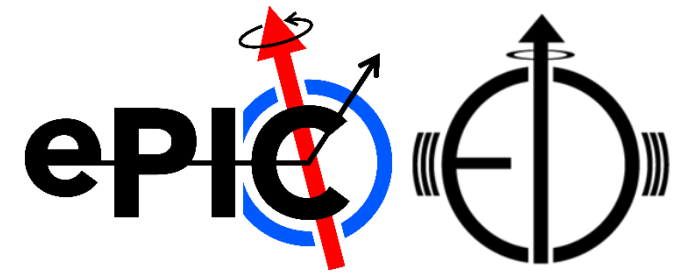


Less dead space (more material):

Layer 3 (EIC-LAS w. 6*RSU) – less dead space, more material

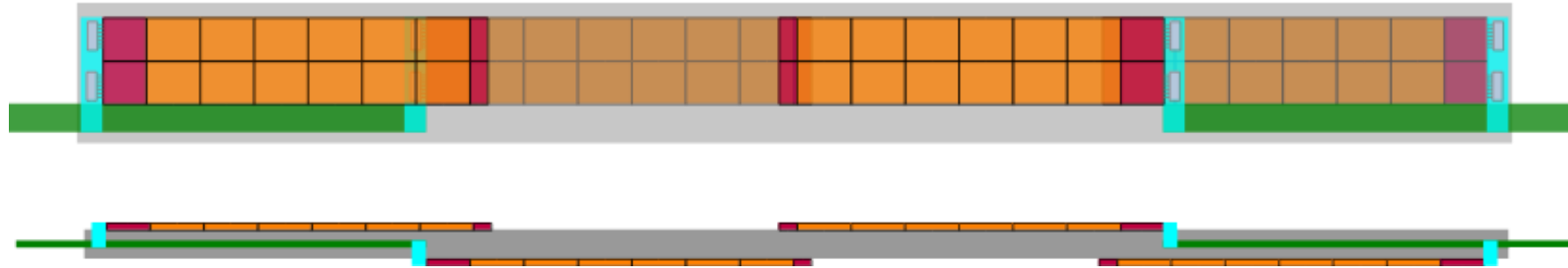


Compare L3 (1-sided readout)



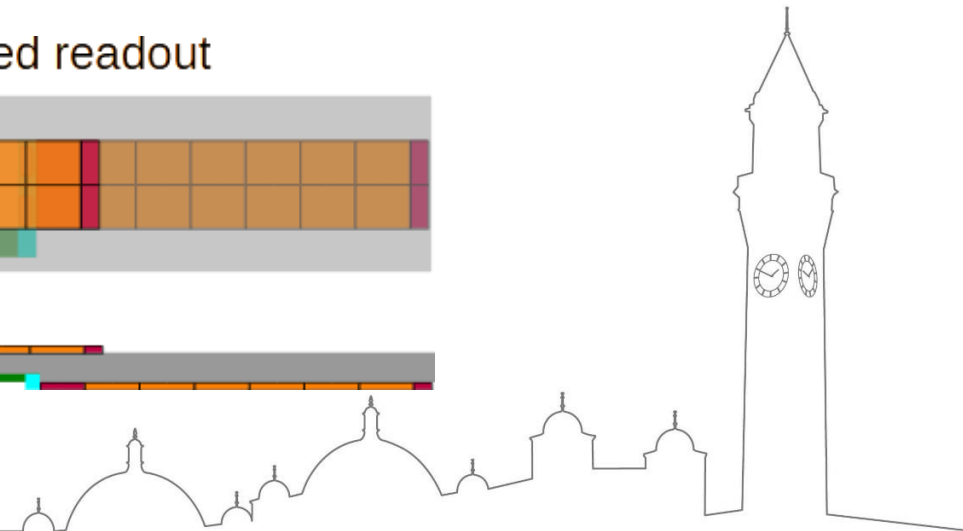
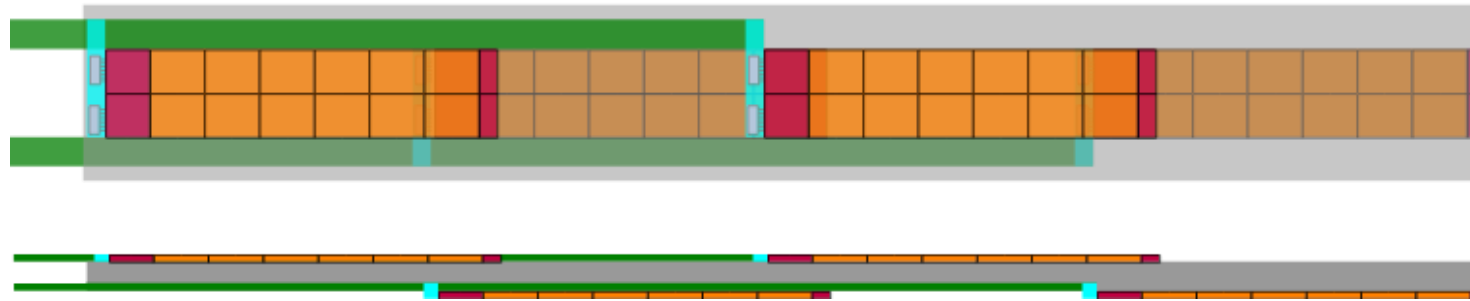
Previous groupings:

Layer 3 (EIC-LAS w. 6*RSU)

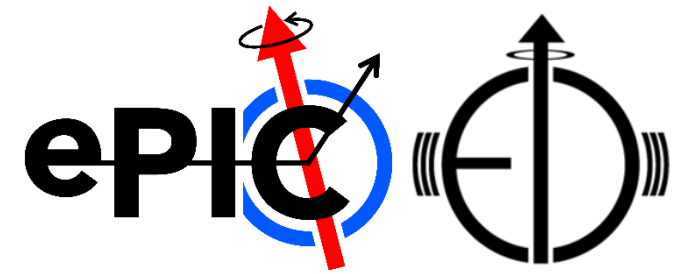


1-sided readout:

Layer 3 (EIC-LAS w. 6*RSU) – 1-sided readout

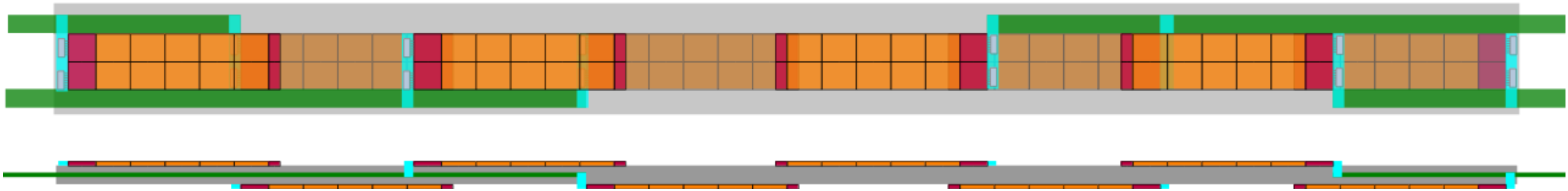


Compare L4



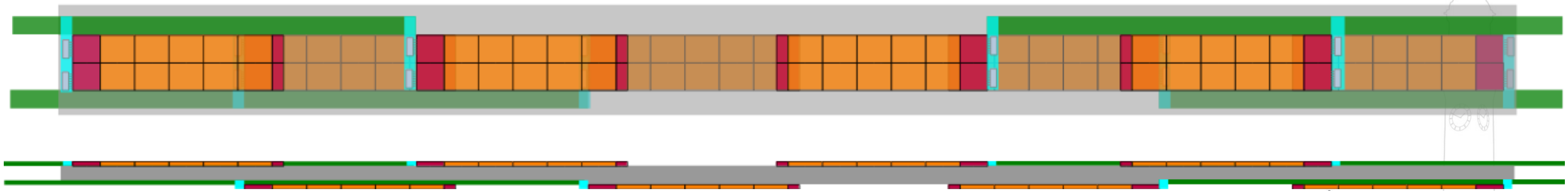
Previous groupings:

Layer 4 (EIC-LAS w. 5*RSU)

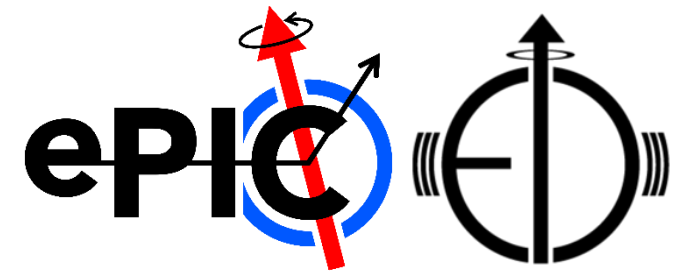


New groupings (FPC change only):

Layer 4 (EIC-LAS w. 5*RSU)

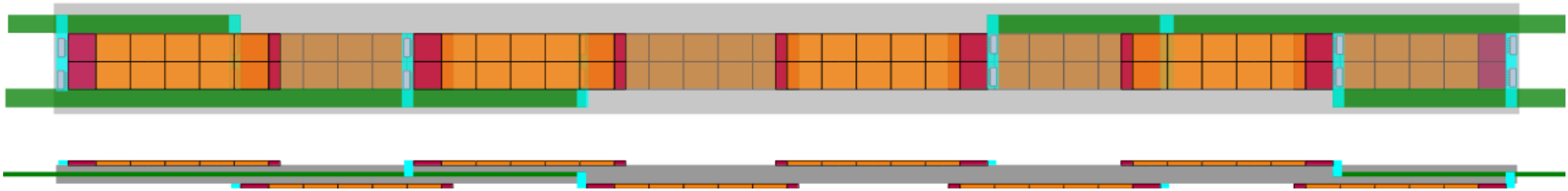


Compare L4



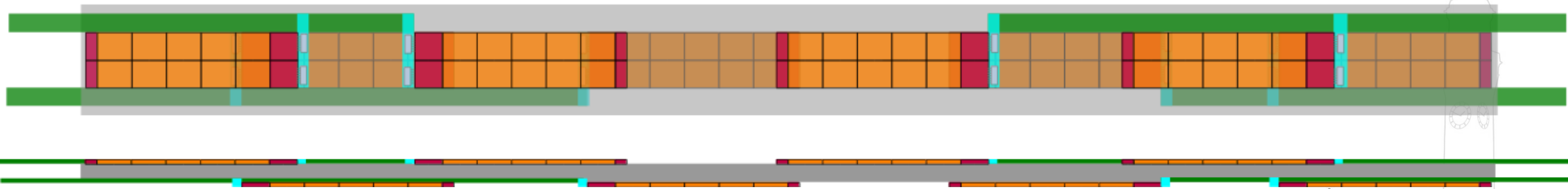
Previous groupings:

Layer 4 (EIC-LAS w. 5*RSU)

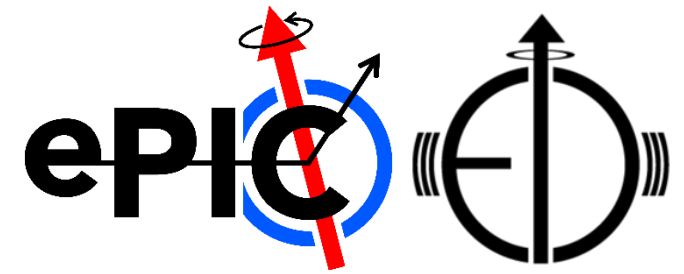


New groupings (complex FPC, less dead space):

Layer 4 (EIC-LAS w. 5*RSU)

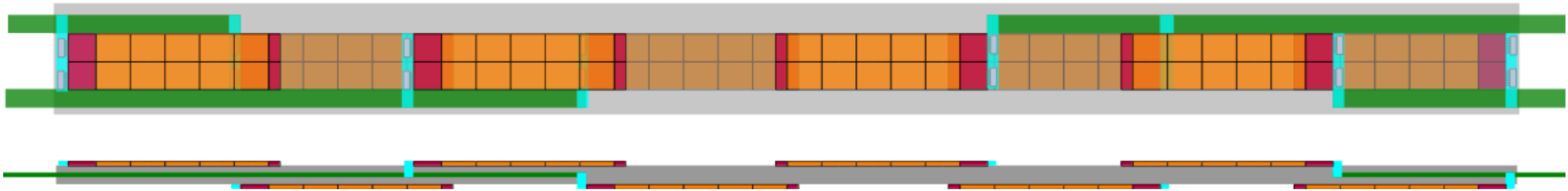


Compare L4



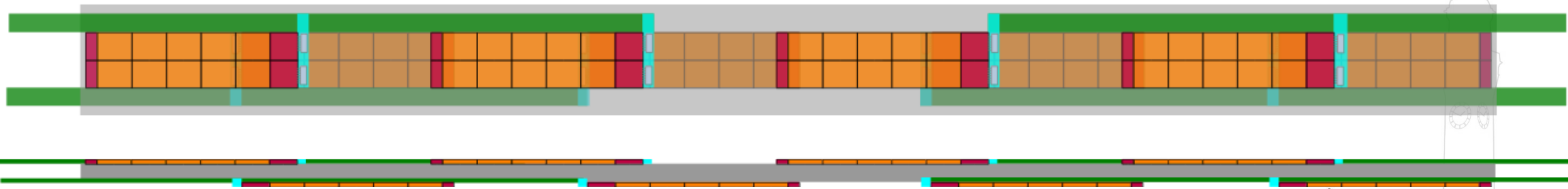
Previous groupings:

Layer 4 (EIC-LAS w. 5*RSU)

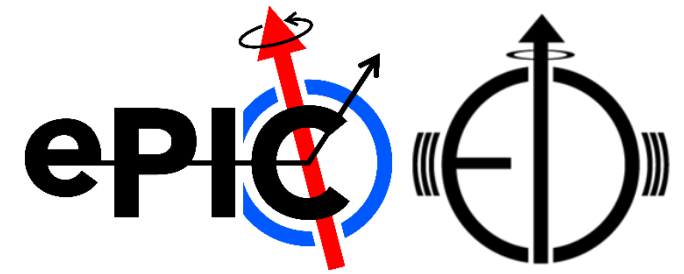


New groupings (simpler FPC, less dead space):

Layer 4 (EIC-LAS w. 5*RSU)

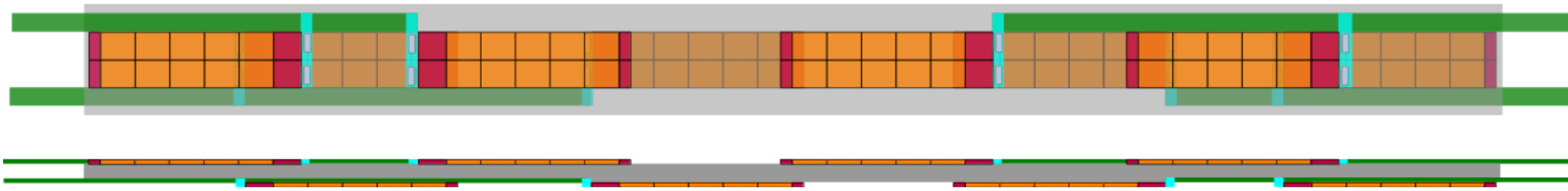


Compare L4 (less dead space)



Complex FPC:

Layer 4 (EIC-LAS w. 5*RSU)



Simpler FPC:

Layer 4 (EIC-LAS w. 5*RSU)

